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# 1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Val	Unit	
		TO-220/DPAK/ IPAK	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	80	00	V
V <sub>GS</sub>	Gate-source voltage	±;	30	V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25°C	3	3 (1)	Α
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> =100°C	1.89 1.89 <sup>(1)</sup>		Α
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	12	12 <sup>(1)</sup>	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25°C	80	25	W
	Derating factor	0.64	0.21	W/°C
V <sub>ESD(G-S)</sub>	Gate source ESD (HBM-C=100pF, R=1.5KΩ)	3000		٧
dv/dt (3)	Peak diode recovery voltage slope	4.	.5	V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; $T_c$ = 25°C)	- 2500		V
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to	°C	

- 1. Limited only by maximum temperature allowed
- 2. Pulse width limited by safe operating area
- 3.  $I_{SD} \le 4A$ , di/dt  $\le 200A/\mu s$ ,  $V_{DD} \le V_{(BR)DSS}$ ,  $T_j \le T_{JMAX}$ .

Table 2. Thermal data

Symbol	Parameter		Value		
		TO-220	TO-220FP	DPAK IPAK	
R <sub>thj-case</sub>	Thermal resistance junction- case max	1.56	5	1.56	°C/W
R <sub>thj-a</sub>	Thermal resistance junction- ambient max	62.5		100	°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose		300		°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	3	Α
E <sub>AS</sub>	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=50V)	190	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
BV <sub>GSO</sub>	Gate-source breakdown voltage	Igs=± 1mA (Open Drain)	30			V

### 1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2 Electrical characteristics

(T<sub>CASE</sub>=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	800			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = Max rating, $V_{DS}$ = Max rating, $T_{C}$ = 125°C			1 50	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>GS</sub> = 0)	V <sub>GS</sub> = ± 20V			±10	μΑ
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\mu A$	3	3.75	4.5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	$V_{GS} = 10V, I_D = 1.5 A$		3	3.5	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} = 15V, I_D = 1.5A$		2.9		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS}$ =25V, f=1 MHz, $V_{GS}$ =0		575 67 13		pF pF pF
C <sub>osseq</sub> (2)	Equivalent output capacitance	V <sub>GS</sub> =0, V <sub>DS</sub> =0V to 400V		60		pF
$t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f}$	Turn-on delay time Rise time Off-voltage rise time Fall time	$V_{DD}$ =400 V, $I_{D}$ = 1.5 A, $R_{G}$ =4.7 $\Omega$ , $V_{GS}$ =10V (see <i>Figure 18</i> )		13 12 35 32		ns ns ns
t <sub>r(Voff)</sub> t <sub>r</sub> t <sub>c</sub>	Off-voltage rise time Fall time Cross-over time	$V_{DD}$ =640 V, $I_D$ = 3 A, $R_G$ =4.7 $\Omega$ , $V_{GS}$ =10V (see <i>Figure 16</i> )		18 7.5 25		ns ns ns
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}$ =640V, $I_{D}$ = 3 A $V_{GS}$ =10V (see <i>Figure 19</i> )		22.5 4.2 11.3		nC nC nC

<sup>1.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

<sup>2.</sup>  $C_{oss\ eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ 

Table 7. Source drain diode

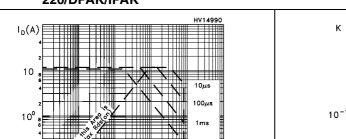
Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current				3	Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)				12	Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	I <sub>SD</sub> = 3 A, V <sub>GS</sub> =0			1.6	٧
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ = 3 A, $di/dt$ = 100A/ $\mu$ s, $V_{DD}$ =80 V, Tj=150°C (see <i>Figure 20</i> )		400 1520 7.6		ns μC A

<sup>1.</sup> Pulse width limited by safe operating area

<sup>2.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/DPAK/IPAK



Tc=25°C

Figure 2. Thermal impedance for TO-220/DPAK/IPAK

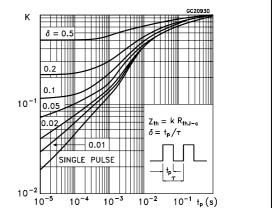


Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

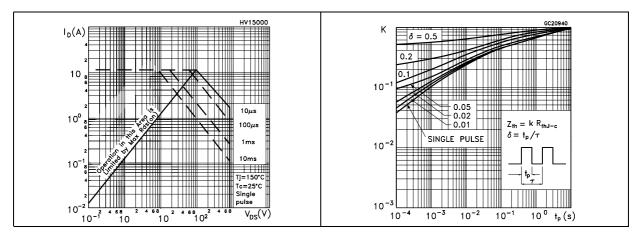
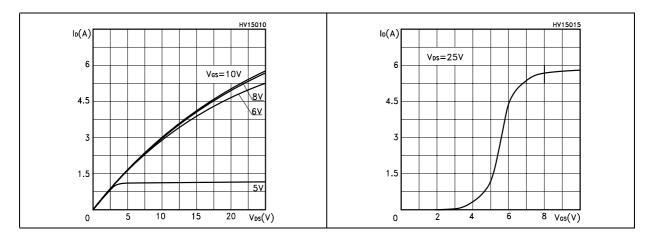


Figure 5. Output characterisics

Figure 6. Transfer characteristics



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Figure 7. Transconductance

Figure 8. Static drain-source on resistance

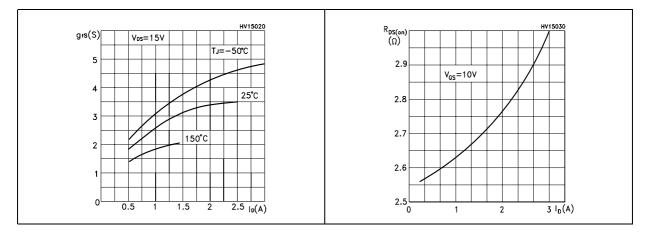


Figure 9. Gate charge vs gate-source voltage Figure 10. Capacitance variations

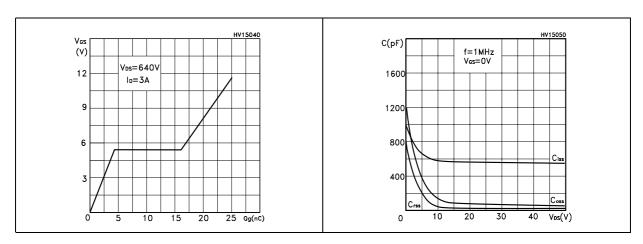


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized BVdss vs temperature

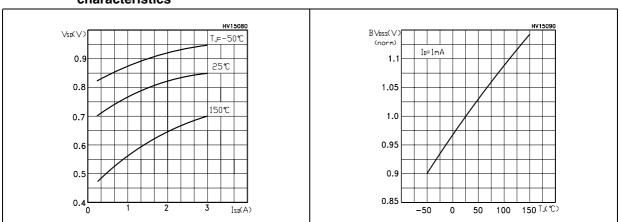


Figure 13. Normalized gate threshold voltage Figure 14. Avalanche energy vs temperature vs temperature

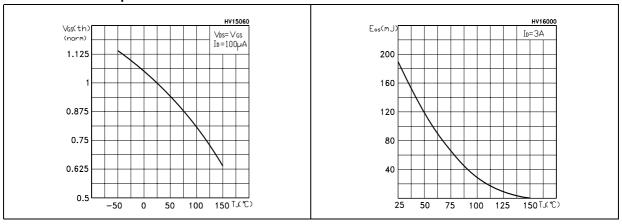
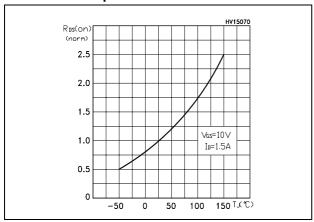


Figure 15. Normalized on resistance vs temperature



## 3 Test circuit

Figure 16. Unclamped Inductive load test circuit

Figure 17. Unclamped Inductive waveform

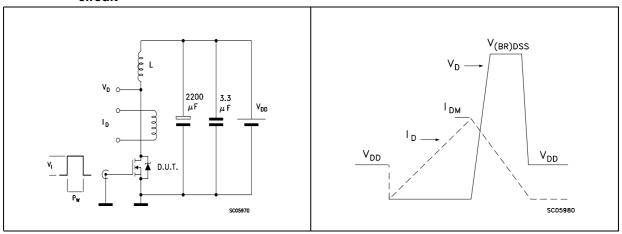


Figure 18. Switching times test circuit for resistive load

Figure 19. Gate charge test circuit

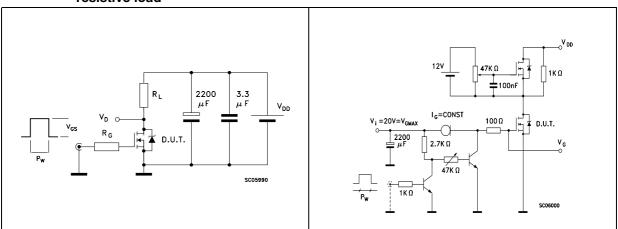
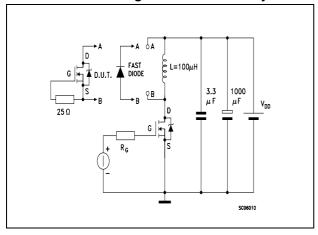


Figure 20. Test circuit for inductive load switching and diode recovery times



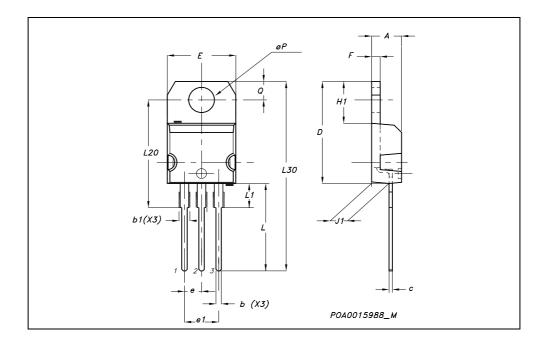
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## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

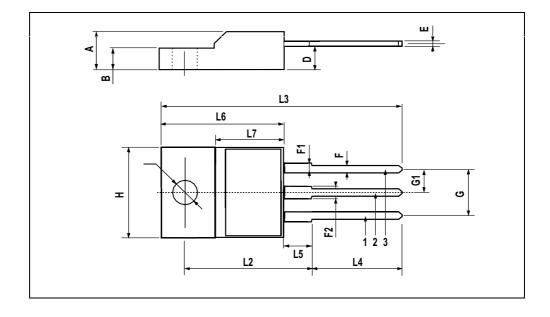
#### **TO-220 MECHANICAL DATA**

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
Е	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



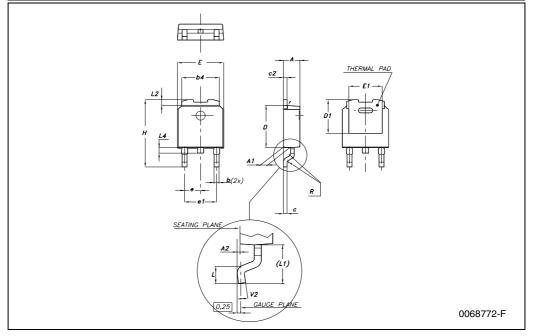
### **TO-220FP MECHANICAL DATA**

DIM		mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	4.4		4.6	0.173		0.181	
В	2.5		2.7	0.098		0.106	
D	2.5		2.75	0.098		0.108	
Е	0.45		0.7	0.017		0.027	
F	0.75		1	0.030		0.039	
F1	1.15		1.7	0.045		0.067	
F2	1.15		1.7	0.045		0.067	
G	4.95		5.2	0.195		0.204	
G1	2.4		2.7	0.094		0.106	
Н	10		10.4	0.393		0.409	
L2		16			0.630		
L3	28.6		30.6	1.126		1.204	
L4	9.8		10.6	.0385		0.417	
L5	2.9		3.6	0.114		0.141	
L6	15.9		16.4	0.626		0.645	
L7	9		9.3	0.354		0.366	
Ø	3		3.2	0.118		0.126	

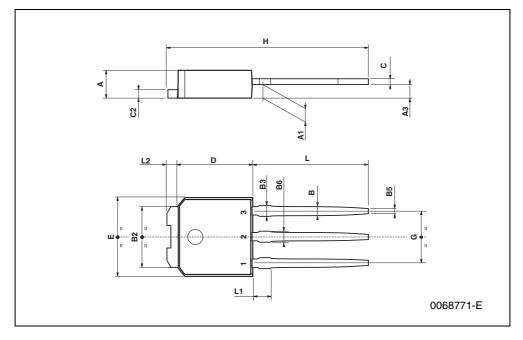


### **DPAK MECHANICAL DATA**

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

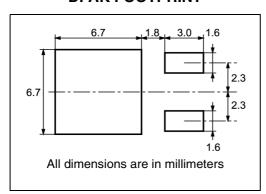


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
В	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
Н	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

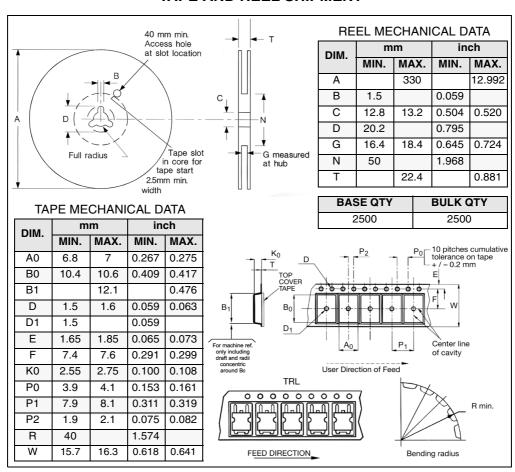


## 5 Packaging mechanical data

#### **DPAK FOOTPRINT**



#### TAPE AND REEL SHIPMENT



# 6 Revision history

Table 8. Revision history

Date	Revision	Changes
30-Mar-2005	5	Preliminary version
06-Sep-2005	6	Final version
21Jan-2006	7	Inserted ecopack indication
16-Aug-2006	8	New template, no content change

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